



## 23rd RD50 Workshop (CERN)

### Wednesday 13 November 2013

#### Defect and Pad Detector Characterization (10:10 - 12:21)

-Conveners: Eckhart Fretwurst

time	[id] title	presenter
10:10	[15] PECULIARITIES OF DARK CONDUCTIVITY IN IRRADIATED SILICON (not Friday)	Prof. VAITKUS, Juozas
10:30	[23] Initial acceptor removal in p-type silicon detectors	KRAMBERGER, Gregor
10:50	[14] Preliminary results on measurements of surface recombination velocity on SLIM edges passivated Si (not Friday)	Prof. VAITKUS, Juozas
11:10	Coffee Break	
11:30	[45] Particulas Demonstration of a Commercial TCT system	KRAMBERGER, Gregor
11:41	[8] Systematic investigation of p-irradiated Micron pad detectors of different silicon materials	NEUGEBAUER, Hannes
12:01	[38] Discussion on Defect and Sensor Characterization	FRETWURST, Eckhart